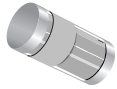
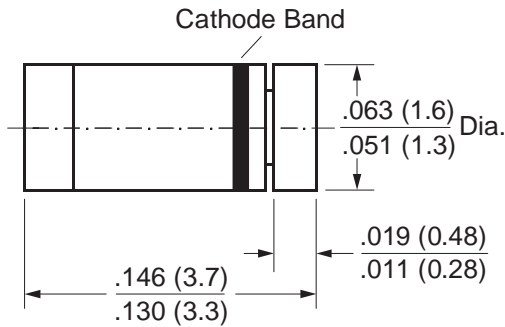




## Schottky Diodes



MiniMELF (SOD-80C)



Dimensions in inches and (millimeters)

### Features

- For general purpose applications
- The LL103A, B, C series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
- The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other applications are click suppression, efficient full wave bridges in telephone subsets, and blocking diodes in rechargeable low voltage battery systems.
- This diode is also available in the DO-35 case with type designation SD103A, B, C and in the SOD-123 case with type designation SD103AW, SD103BW, SD103CW.

### Mechanical Data

**Case:** MiniMELF Glass Case (SOD-80C)

**Weight:** approx. 0.05g

**Cathode Band Color:** Green

**Packaging Codes/Options:**

D1/10K per 13" reel (8mm tape), 20K/box

D2/2.5K per 7" reel (8mm tape), 20K/box

### Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Peak Inverse Voltage	$V_{RRM}$	40 30 20	V
Power Dissipation (Infinite Heatsink)	$P_{tot}$	400 <sup>(1)</sup>	mW
Single Cycle Surge 60-Hz Sine Wave	$I_{FSM}$	15	A
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	300 <sup>(1)</sup>	°CW
Junction Temperature	$T_j$	125	°C
Storage Temperature Range	$T_s$	-55 to +150	°C

### Electrical Characteristics ( $T_j = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Leakage Current	$I_R$	$V_R = 30V$ $V_R = 20V$ $V_R = 10V$	—	—	5 5 5	$\mu A$
Forward Voltage Drop	$V_F$	$I_F = 20mA$ $I_F = 200mA$	—	—	0.37 0.6	V
Junction Capacitance	$C_{tot}$	$V_R = 0V, f = 1MHz$	—	50	—	pF
Reverse Recovery Time	$t_{rr}$	$I_F = I_R = 50mA$ to 200mA, recover to 0.1I <sub>R</sub>	—	—	10	ns

**Note:** (1) Valid provided that electrodes are kept at ambient temperature.

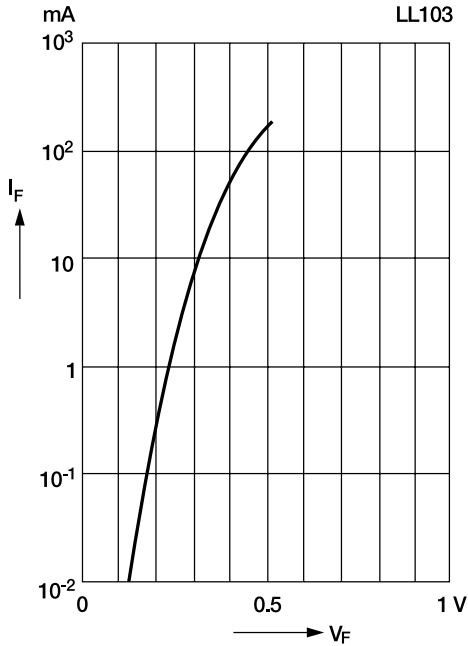
# LL103A thru LL103C

Vishay Semiconductors  
formerly General Semiconductor

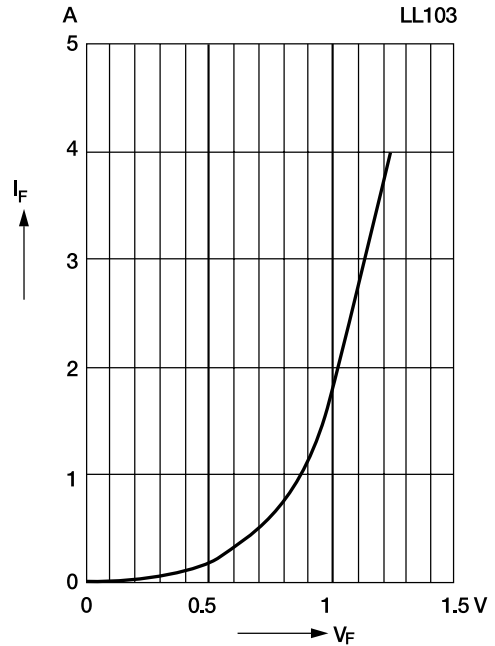


## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

**Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier**

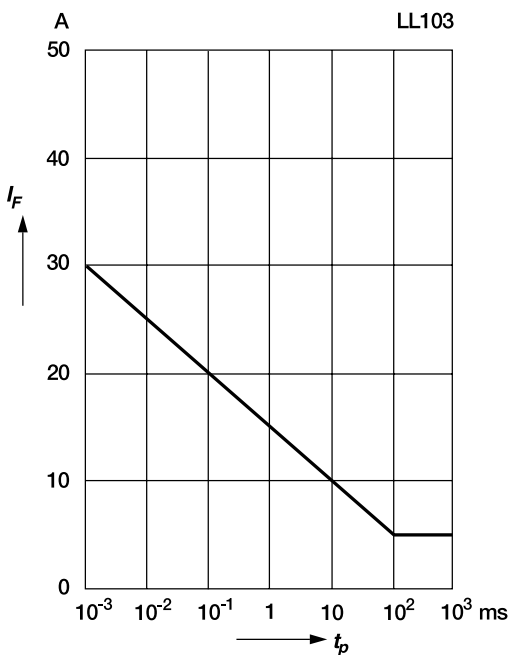


**Typical high current forward conduction curve**  
 $t_p = 300$  ms, duty cycle = 2%

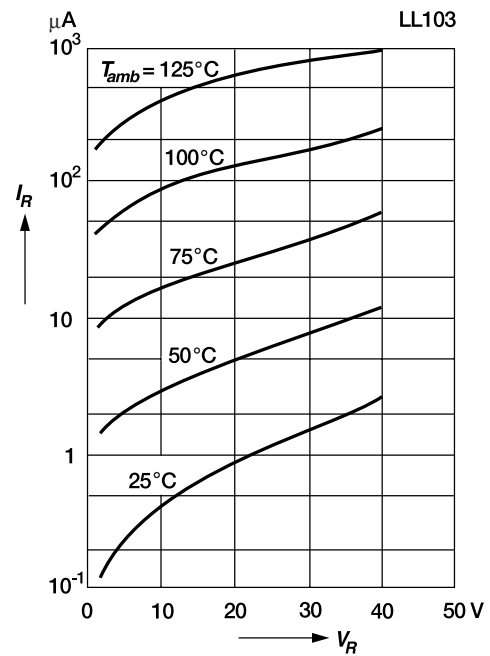


**Typical non repetitive forward surge current versus pulse width**

Rectangular pulse



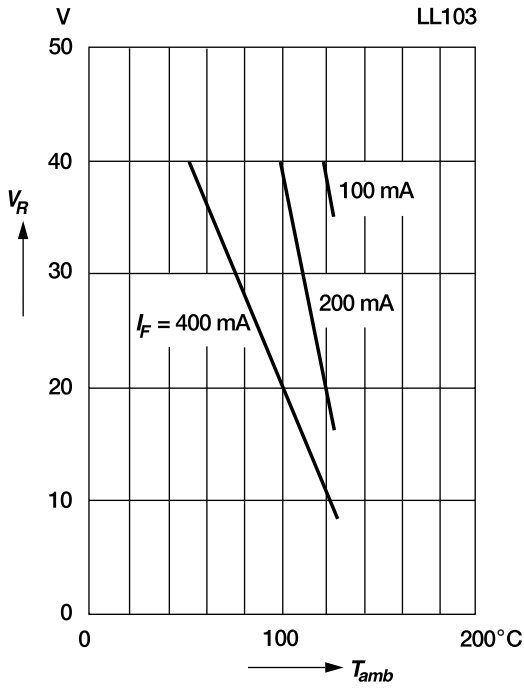
**Typical variation of reverse current at various temperatures**





**Ratings and  
Characteristic Curves** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

**Blocking voltage deration  
versus temperature at various  
average forward currents**



**Typical capacitance  
versus reverse voltage**

